

TC1221/TC1222

High Frequency Switched Capacitor Voltage Converters with Shutdown in SOT Packages

Features

- Charge Pumps in 6-Pin SOT-23A Package
- 96% Voltage Conversion Efficiency
- Voltage Inversion and/or Doubling
- Operates from +1.8V to +5.5V
- Up to 25mA Output Current
- · Only Two External Capacitors Required
- · Power-Saving Shutdown Mode
- Fully Compatible with 1.8V Logic Systems

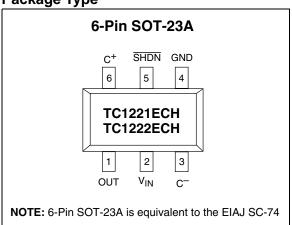
Applications

- · LCD Panel Bias
- · Cellular Phones
- Pagers
- · PDAs, Portable Data Loggers
- · Battery-Powered Devices

Device Selection Table

Part Number	Package	Osc. Freq. (kHz)	Operating Temp. Range
TC1221ECH	6-Pin SOT-23A	125	-40°C to +85°C
TC1222ECH	6-Pin SOT-23A	750	-40°C to +85°C

Package Type



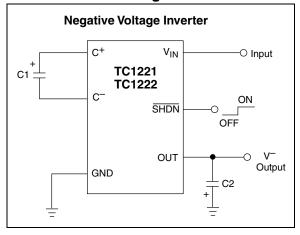
General Description

The TC1221/TC1222 are CMOS "charge-pump" voltage converters in ultra-small 6-Pin SOT-23A packages. They invert and/or double an input voltage which can range from +1.8V to +5.5V. Conversion efficiency is typically 96%. Switching frequency is 125kHz for the TC1221, 750kHz for the TC1222. When the shutdown pin is held at a logic low, the device goes into a very low power mode of operation, consuming less than $1\mu A$ of supply current.

For standard voltage inverter applications, the device requires only two external capacitors. With a few additional components a positive doubler can also be built. All other circuitry, including control, oscillator, power MOSFETs are integrated on-chip. Typical supply currents are 290µA (TC1221) and 1800µA (TC1222).

All devices are available in 6-pin SOT-23A surface mount packages.

Functional Block Diagram



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings*

 $\label{eq:local_$

*Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

TC1121 ELECTRICAL SPECIFICATIONS

Electrical Characteristics: $T_A = -40^{\circ}\text{C}$ to +85°C, $V_{IN} = +5\text{V}$, C1 = C2 = 1 μ F, (TC1221), C1 = C2 = 0.22 μ F (TC1222), Typical values are at $T_A = +25^{\circ}\text{C}$.

Symbol	Parameter	Min	Тур	Max	Units	Device	Test Conditions
I _{DD}	Supply Current		290 1800	600 2800	μА	TC1221 TC1222	
I _{SHDN}	Shutdown Supply Current	_	0.01	1.0	μА		SHDN = GND, V _{IN} = 5V (Note 2)
V _{MIN}	Minimum Supply Voltage	1.8	_	_	V		$R_{LOAD} = 1k\Omega$
V _{MAX}	Maximum Supply Voltage	_	_	5.5	V		$R_{LOAD} = 1k\Omega$
Fosc	Oscillator Frequency	81 550	125 750	169 950	kHz	TC1221 TC1222	
V _{IH}	SHDN Input Logic High	1.4		_	V		$V_{IN} = V_{MIN}$ to V_{MAX}
V _{IL}	SHDN Input Logic Low	_	_	0.4	V		$V_{IN} = V_{MIN}$ to V_{MAX}
P _{EFF}	Power Efficiency		90 70		%	TC1221 TC1222	$R_{LOAD} = 1k\Omega$
V _{EFF}	Voltage Conversion Efficiency	94	96	_	%		R _{LOAD} = ∞
R _{OUT}	Output Resistance	_ _	25	65	Ω		I _{LOAD} = 0.5mA to 25mA (Note 1)
Twĸ	Wake-up Time From Shutdown Mode	_ _	80 25	_ _	μsec	TC1221 TC1222	$R_{LOAD} = 1k\Omega$

Note 1: Capacitor contribution is approximately 20% of the output impedance [ESR = 1/ pump frequency x capacitance].

^{2:} V_{IN} is guaranteed to be disconnected from OUT when the converter is in shutdown.

2.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 2-1.

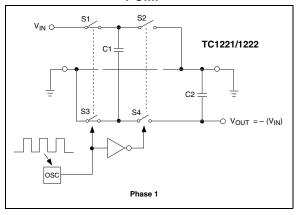
TABLE 2-1: PIN FUNCTION TABLE

Pin No. (6-Pin SOT-23A)	Symbol	Description
1	OUT	Inverting charge pump output.
2	V_{IN}	Positive power supply input.
3	C_	Commutation capacitor negative terminal.
4	GND	Ground.
5	SHDN	Shutdown input (active low).
6	C ⁺	Commutation capacitor positive terminal.

3.0 DETAILED DESCRIPTION

The TC1221/TC1222 charge pump converters invert the voltage applied to the V_{IN} pin. Conversion consists of a two-phase operation (Figure 3-1). During the first phase, switches S2 and S4 are opened and S1 and S3 are closed. During this time, C1 charges to the voltage on V_{IN} and load current is supplied from C2. During the second phase, S2 and S4 are closed, and S1 and S3 are opened. This action connects C1 across C2, restoring charge to C2.

FIGURE 3-1: IDEAL SWITCHED CAPACITOR CHARGE PUMP



4.0 APPLICATIONS INFORMATION

4.1 Output Voltage Considerations

The TC1221/TC1222 perform voltage conversion but do not provide *regulation*. The output voltage will droop in a linear manner with respect to load current. The value of this equivalent output resistance is approximately 25 Ω nominal at +25°C and V_{IN} = +5V. V_{OUT} is approximately -5V at light loads, and droops according to the equation below:

$$V_{DROP} = I_{OUT} \times R_{OUT}$$

 $V_{OUT} = -(V_{IN} - V_{DROP})$

4.2 Charge Pump Efficiency

The overall power efficiency of the charge pump is affected by four factors:

- Losses from power consumed by the internal oscillator, switch drive, etc. (which vary with input voltage, temperature and oscillator frequency).
- I²R losses due to the on-resistance of the MOSFET switches on-board the charge pump.
- Charge pump capacitor losses due to effective series resistance (ESR).
- Losses that occur during charge transfer (from the commutation capacitor to the output capacitor) when a voltage difference between the two capacitors exists.

Most of the conversion losses are due to factors (2) and (3) above. These losses are given by Equation 4-1(b).

EQUATION 4-1:

a)
$$P_{LOSS}(2,3) = I_{OUT}^2 \times R_{OUT}$$

b) where $R_{OUT} = \left[1 / \left[f_{OSC}(C1) \right] + 8R_{SWITCH} + 4ESR_{C1} + ESR_{C2} \right]$

The $1/(f_{OSC})(C1)$ term in Equation 4-1(b) is the effective output resistance of an ideal switched capacitor circuit (Figure 4-1 and Figure 4-2). The value of R_{SWITCH} can be approximated at 0.5Ω for the TC1221/TC1222.

The remaining losses in the circuit are due to factor (4) above, and are shown in Equation 4-2. The output voltage ripple is given by Equation 4-3.

EQUATION 4-2:

$$P_{LOSS}(4) = [(0.5)(C1)(V_{IN}^2 - V_{OUT}^2) + (0.5)$$
$$(C_2)(V_{RIPPLE}^2 - 2V_{OUT} V_{RIPPLE})] \times f_{OSC}$$

EQUATION 4-3:

$$V_{RIPPLE} = [I_{OUT} / 2 x (f_{OSC}) (C2)] + 2 (I_{OUT}) (ESR_{C2})$$

FIGURE 4-1: IDEAL SWITCHED CAPACITOR MODEL

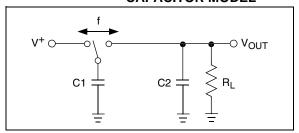
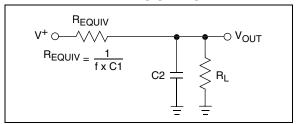


FIGURE 4-2: EQUIVALENT OUTPUT RESISTANCE



4.3 Capacitor Selection

In order to maintain the lowest output resistance and output ripple voltage, it is recommended that low ESR capacitors be used. Additionally, larger values of C1 will lower the output resistance and larger values of C2 will reduce output ripple. (Equation 4-1(b) and Equation 4-3).

Table 4-1 shows various values of C1 and the corresponding output resistance values @ +25°C. It assumes a 0.1 Ω ESR_{C1} and 2 Ω R_{SWITCH}. Table 4-2 shows the output voltage ripple for various values of C2. The V_{RIPPLE} values assume 10mA output load current and 0.1 Ω ESR_{C2}.

TABLE 4-1: OUTPUT RESISTANCE VS. C1 (ESR = 0.1Ω)

C1 (μF)	TC1221 R _{OUT} (Ω)	TC1222 R _{OUT} (Ω)
0.22	52.9	22.6
0.33	40.8	20.5
0.47	33.5	19.4
1.0	25	17.8

TABLE 4-2: OUTPUT VOLTAGE RIPPLE VS. C2 (ESR = 0.1Ω) I_{OUT} 10mA

C2 (μF)	TC1221 V _{RIPPLE} (mV)	TC1222 V _{RIPPLE} (mV)
0.22	184	32
0.33	123	22
0.47	87	16
1.0	42	9

4.4 Input Supply Bypassing

The V_{IN} input should be capacitively bypassed to reduce AC impedance and minimize noise effects due to the internal switching of the device. The recommended capacitor depends on the configuration of the TC1221/TC1222.

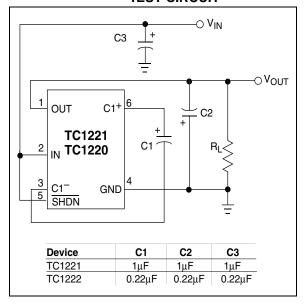
4.5 Shutdown Input

The TC1221/TC1222 is enabled when \overline{SHDN} is high, and disabled when \overline{SHDN} is low. This input cannot be allowed to float. The \overline{SHDN} input should be limited to 0.5V above V_{IN} to avoid significant current flows.

4.6 Voltage Inverter

The most common application for charge pump devices is the inverter (Figure 4-3). This application uses two external capacitors: C1 and C2 (plus a power supply bypass capacitor, if necessary). The output is equal to -V_{IN} plus any voltage drops due to loading. Refer to Table 4-1 and Table 4-2 for capacitor selection.

FIGURE 4-3: VOLTAGE INVERTER TEST CIRCUIT



4.7 Cascading Devices

Two or more TC1221/TC1222 can be cascaded to increase output voltage (Figure 4-4). If the output is lightly loaded, it will be close to (-2 x $V_{\rm IN}$) but will droop at least by $R_{\rm OUT}$ of the first device multiplied by the $I_{\rm Q}$ of the second. It can be seen that the output resistance rises rapidly for multiple cascaded devices.

4.8 Paralleling Devices

To reduce the value of R_{OUT} , multiple TC1221/TC1222's can be connected in parallel (Figure 4-5). The output resistance will be reduced by a factor of N where N is the number of TC1221/TC1222. Each device will require its own pump capacitor (C1), but all devices may share one reservoir capacitor (C2). However, to preserve ripple performance the value of C2 should be scaled according to the number of paralleled TC1221/TC1222.

FIGURE 4-4: CASCADING MULTIPLE DEVICES TO INCREASE OUTPUT VOLTAGE

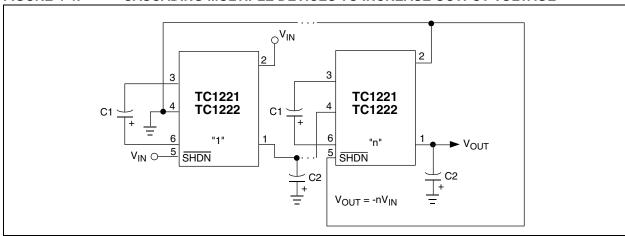
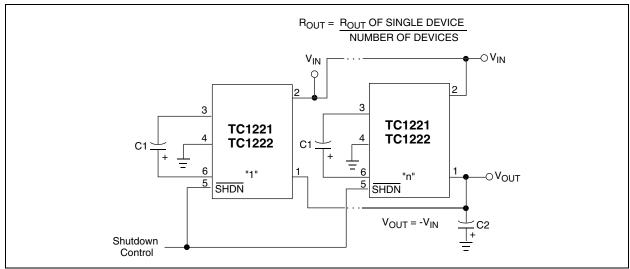


FIGURE 4-5: PARALLELING MULTIPLE DEVICES TO REDUCE OUTPUT RESISTANCE



4.9 Voltage Doubler/Inverter

Another common application of the TC1221/TC1222 is shown in Figure 4-6. This circuit performs two functions in combination. C1 and C2 form the standard inverter circuit described above. C3 and C4 plus the two diodes form the voltage doubler circuit. C1 and C3 are the pump capacitors and C2 and C4 are the reservoir capacitors. Because both sub-circuits rely on the same switches if either output is loaded, both will droop toward GND. Make sure that the total current drawn from both the outputs does not total more than 40mA.

4.10 Diode Protection for Heavy Loads

When heavy loads require the OUT pin to sink large currents being delivered by a positive source, diode protection may be needed. The OUT pin should not be allowed to be pulled above ground. This is accomplished by connecting a Schottky diode (1N5817) as shown in Figure 4-7.

4.11 Layout Considerations

As with any switching power supply circuit, good layout practice is recommended. Mount components as close together as possible to minimize stray inductance and capacitance. Noise leakage into other circuitry can be minimized with the use of a large ground plane.

FIGURE 4-6: COMBINED DOUBLER AND INVERTER

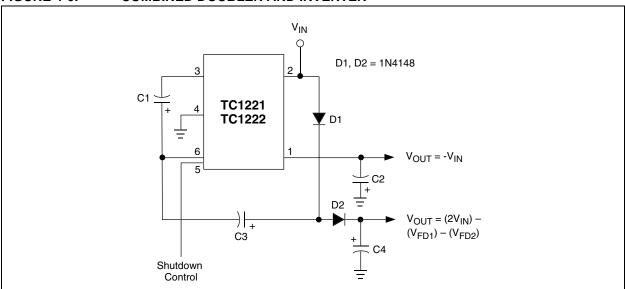
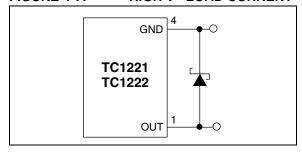


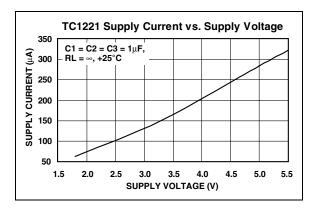
FIGURE 4-7: HIGH V- LOAD CURRENT

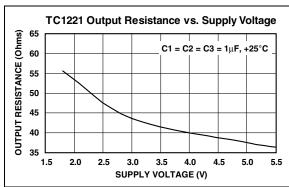


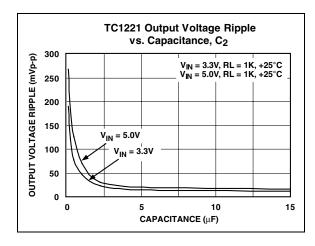
5.0 TYPICAL CHARACTERISTICS

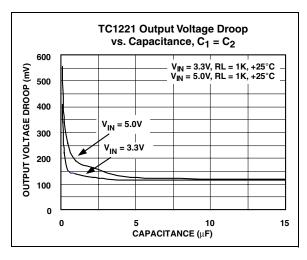
Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

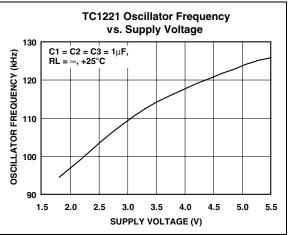
Circuit of Figure 4-3, V_{IN} = +5V, C1 = C2 = C3, T_A = 25°C unless otherwise noted.



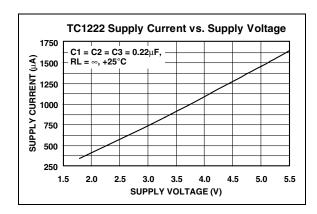


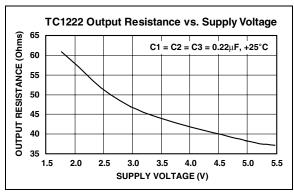


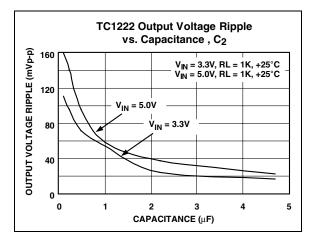


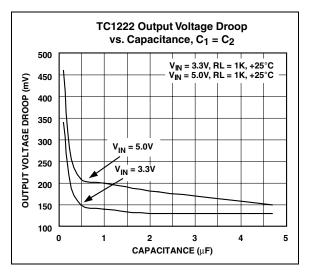


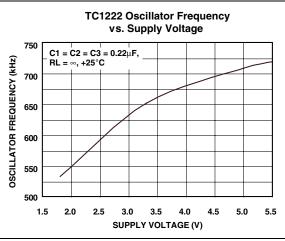
5.0 TYPICAL CHARACTERISTICS (CONTINUED)





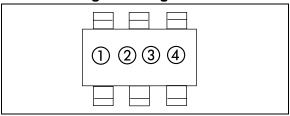






6.0 **PACKAGING INFORMATION**

6.1 **Package Marking Information**



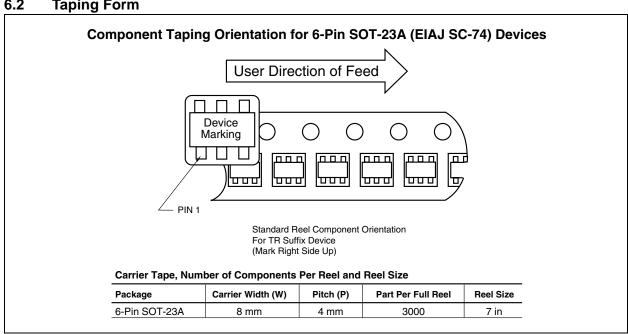
① & ② = part number code + temperature range (two-digit code)

TC1221/TC1222 Code TC1221ECH GΑ TC1222ECH GB

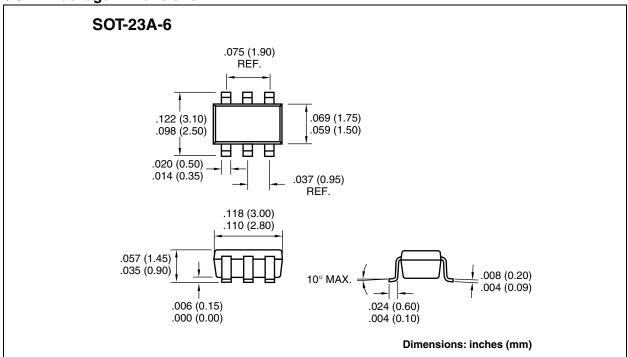
ex: 1221ECH = (A () (1222ECH = @ B () ()

- 3 represents year and 2-month code
- ④ represents production lot ID code

6.2 **Taping Form**



6.3 Package Dimensions



Sales and Support

Data Sheets

Products supported by a preliminary Data Sheet may have an errata sheet describing minor operational differences and recommended workarounds. To determine if an errata sheet exists for a particular device, please contact one of the following:

- Your local Microchip sales office The Microchip Corporate Literature Center U.S. FAX: (480) 792-7277
- The Microchip Worldwide Site (www.microchip.com)

Please specify which device, revision of silicon and Data Sheet (include Literature #) you are using.

New Customer Notification System

Register on our web site (www.microchip.com/cn) to receive the most current information on our products.

TC1221/TC1222

NOTES:

Information contained in this publication regarding device applications and the like is intended through suggestion only and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. No representation or warranty is given and no liability is assumed by Microchip Technology Incorporated with respect to the accuracy or use of such information, or infringement of patents or other intellectual property rights arising from such use or otherwise. Use of Microchip's products as critical components in life support systems is not authorized except with express written approval by Microchip. No licenses are conveyed, implicitly or otherwise, under any intellectual property rights.

Trademarks

The Microchip name and logo, the Microchip logo, FilterLab, KEELOQ, microID, MPLAB, PIC, PICmicro, PICMASTER, PICSTART, PRO MATE, SEEVAL and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

dsPIC, ECONOMONITOR, FanSense, FlexROM, fuzzyLAB, In-Circuit Serial Programming, ICSP, ICEPIC, microPort, Migratable Memory, MPASM, MPLIB, MPLINK, MPSIM, MXDEV, PICC, PICDEM, PICDEM.net, rfPIC, Select Mode and Total Endurance are trademarks of Microchip Technology Incorporated in the U.S.A.

Serialized Quick Turn Programming (SQTP) is a service mark of Microchip Technology Incorporated in the U.S.A.

All other trademarks mentioned herein are property of their respective companies.

© 2002, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.





Microchip received QS-9000 quality system certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona in July 1999 and Mountain View, California in March 2002. The Company's quality system processes and procedures are QS-9000 compliant for its PICmicro® 8-bit MCUs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, non-volatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001 certified.



WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 Technical Support: 480-792-7627 Web Address: http://www.microchip.com

Rocky Mountain

2355 West Chandler Blvd. Chandler, AZ 85224-6199
Tel: 480-792-7966 Fax: 480-792-7456

Atlanta

500 Sugar Mill Road, Suite 200B Atlanta, GA 30350 Tel: 770-640-0034 Fax: 770-640-0307

Boston

2 Lan Drive, Suite 120 Westford, MA 01886 Tel: 978-692-3848 Fax: 978-692-3821

Chicago

333 Pierce Road, Suite 180 Itasca, IL 60143

Tel: 630-285-0071 Fax: 630-285-0075

Dallas

4570 Westgrove Drive, Suite 160 Addison, TX 75001 Tel: 972-818-7423 Fax: 972-818-2924

Detroit

Tri-Atria Office Building 32255 Northwestern Highway, Suite 190 Farmington Hills, MI 48334 Tel: 248-538-2250 Fax: 248-538-2260

Kokomo

2767 S. Albright Road Kokomo, Indiana 46902 Tel: 765-864-8360 Fax: 765-864-8387

Los Angeles

18201 Von Karman, Suite 1090 Irvine, CA 92612

Tel: 949-263-1888 Fax: 949-263-1338

New York

150 Motor Parkway, Suite 202 Hauppauge, NY 11788 Tel: 631-273-5305 Fax: 631-273-5335

San Jose

Microchip Technology Inc. 2107 North First Street, Suite 590 San Jose, CA 95131 Tel: 408-436-7950 Fax: 408-436-7955

Toronto

6285 Northam Drive, Suite 108 Mississauga, Ontario L4V 1X5, Canada Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

Australia

Microchip Technology Australia Pty Ltd Suite 22, 41 Rawson Street Epping 2121, NSW Australia

Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

China - Beijing

Microchip Technology Consulting (Shanghai) Co., Ltd., Beijing Liaison Office Unit 915

Bei Hai Wan Tai Bldg. No. 6 Chaoyangmen Beidajie Beijing, 100027, No. China Tel: 86-10-85282100 Fax: 86-10-85282104

China - Chengdu

Microchip Technology Consulting (Shanghai) Co., Ltd., Chengdu Liaison Office Rm. 2401, 24th Floor, Ming Xing Financial Tower No. 88 TIDU Street Chengdu 610016, China Tel: 86-28-6766200 Fax: 86-28-6766599

China - Fuzhou

Microchip Technology Consulting (Shanghai) Co., Ltd., Fuzhou Liaison Office Unit 28F, World Trade Plaza No. 71 Wusi Road Fuzhou 350001, China Tel: 86-591-7503506 Fax: 86-591-7503521

China - Shanghai

Microchip Technology Consulting (Shanghai) Co., Ltd. Room 701, Bldg. B

Far East International Plaza No. 317 Xian Xia Road Shanghai, 200051

Tel: 86-21-6275-5700 Fax: 86-21-6275-5060

China - Shenzhen

Microchip Technology Consulting (Shanghai) Co., Ltd., Shenzhen Liaison Office Rm. 1315, 13/F, Shenzhen Kerry Centre, Renminnan Lu Shenzhen 518001, China Tel: 86-755-2350361 Fax: 86-755-2366086

Hong Kong

Microchip Technology Hongkong Ltd. Unit 901-6, Tower 2, Metroplaza 223 Hing Fong Road Kwai Fong, N.T., Hong Kong Tel: 852-2401-1200 Fax: 852-2401-3431

India

Microchip Technology Inc. India Liaison Office Divvasree Chambers 1 Floor, Wing A (A3/A4) No. 11, O'Shaugnessey Road Bangalore, 560 025, India Tel: 91-80-2290061 Fax: 91-80-2290062

Japan

Microchip Technology Japan K.K. Benex S-1 6F 3-18-20, Shinyokohama Kohoku-Ku, Yokohama-shi Kanagawa, 222-0033, Japan Tel: 81-45-471- 6166 Fax: 81-45-471-6122

Korea

Microchip Technology Korea 168-1, Youngbo Bldg. 3 Floor Samsung-Dong, Kangnam-Ku Seoul, Korea 135-882

Tel: 82-2-554-7200 Fax: 82-2-558-5934

Singapore

Microchip Technology Singapore Pte Ltd. 200 Middle Road #07-02 Prime Centre Singapore, 188980

Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan

Microchip Technology Taiwan 11F-3, No. 207 Tung Hua North Road Taipei, 105, Taiwan Tel: 886-2-2717-7175 Fax: 886-2-2545-0139

EUROPE

Denmark

Microchip Technology Nordic ApS Regus Business Centre Lautrup hoj 1-3 Ballerup DK-2750 Denmark Tel: 45 4420 9895 Fax: 45 4420 9910

France

Microchip Technology SARL Parc d'Activite du Moulin de Massy 43 Rue du Saule Trapu Batiment A - Ier Etage 91300 Massy, France Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany Microchip Technology GmbH Gustav-Heinemann Ring 125 D-81739 Munich, Germany Tel: 49-89-627-144 0 Fax: 49-89-627-144-44 Italy

Microchip Technology SRL

Centro Direzionale Colleoni Palazzo Taurus 1 V. Le Colleoni 1 20041 Agrate Brianza Milan, Italy Tel: 39-039-65791-1 Fax: 39-039-6899883

United Kingdom

Arizona Microchip Technology Ltd. 505 Eskdale Road Winnersh Triangle Wokingham Berkshire, England RG41 5TU Tel: 44 118 921 5869 Fax: 44-118 921-5820

03/01/02

